

HIGH ENERGY PROTON DECHANNELING IN SILICON CRYSTALS

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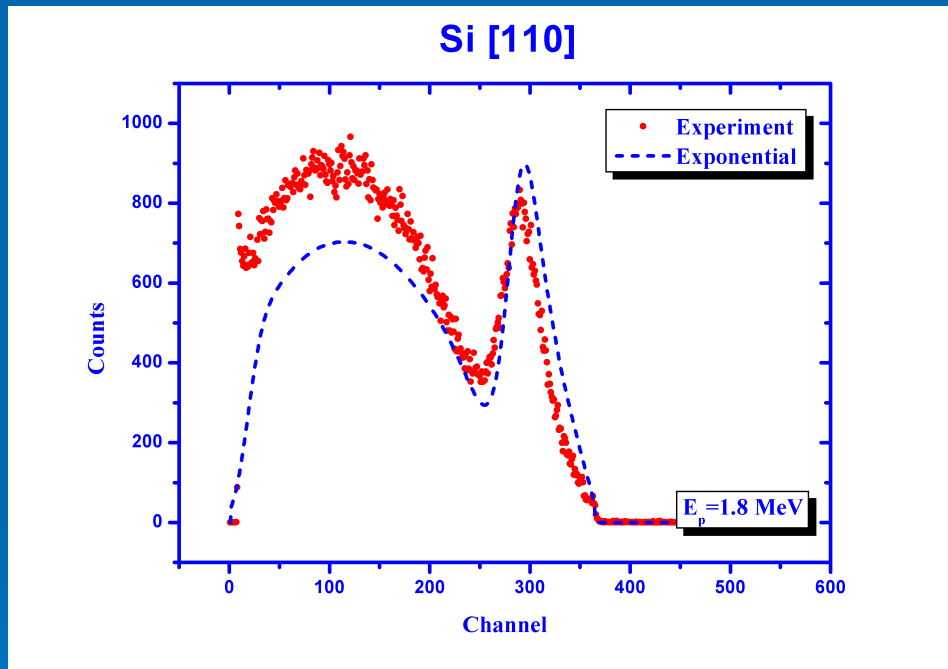


OUTLINE OF THE TALK

- Formulation of the dechanneling problem
- Theory of the dechanneling
- Results and perspective

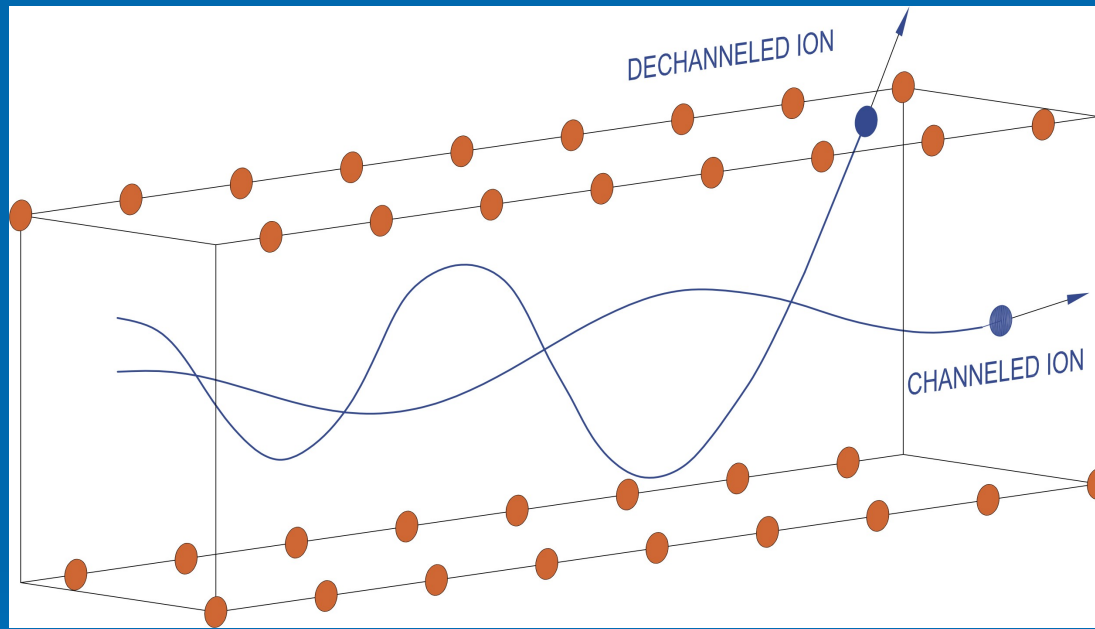


Formulation of the dechanneling problem



1. Energy loss of protons in silicon in the $\langle 110 \rangle$ direction, $S_{\text{ch}} = \alpha S_{\text{ran}}$, $\alpha = \text{const.}$
2. Exponential dechanneling function.

Ion dechanneling effect

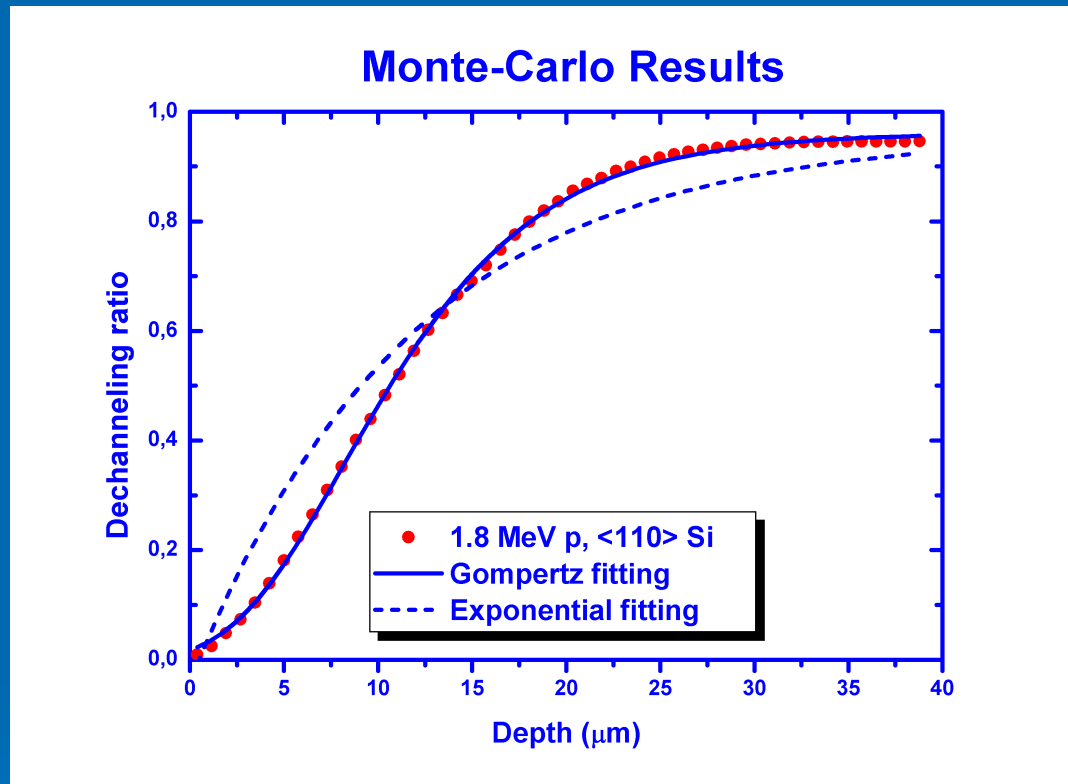


Dechanneling function represents the number of dechanneled ions with respect to the total number of channeled ions (dechanneling ratio) after some crystal depth.

Theory of the dechanneling

- The dechanneling function is generated by a realistic Monte-Carlo computer simulation code using the numerical solution of the proton equations of motion in the transverse plane.
- Continuum approximation is assumed with the continuum potential obtained from the Moliere's ion-atom interaction potential.
- Thermal vibrations of the crystal atoms, the energy loss of the proton and proton-electron multiple scattering are included in the code.
- The obtained dechanneling function is fitted with the appropriate analytical expression.

Gomperz type sigmoidal dechanneling function



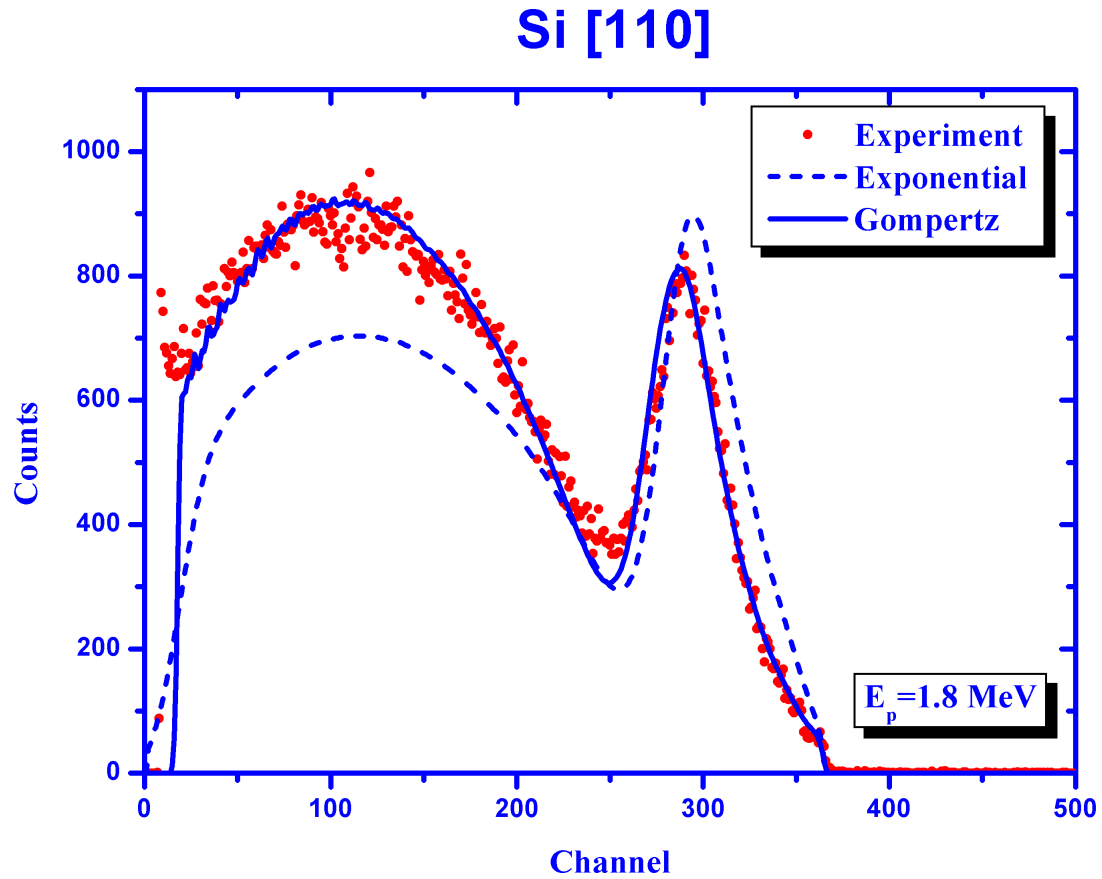
**Gompertz
dechanneling function**

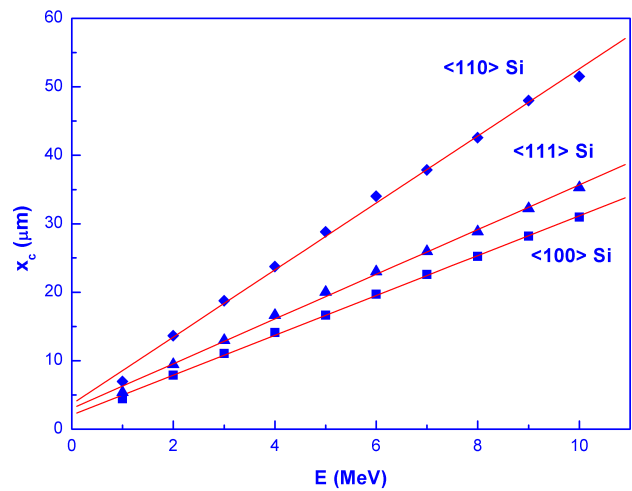
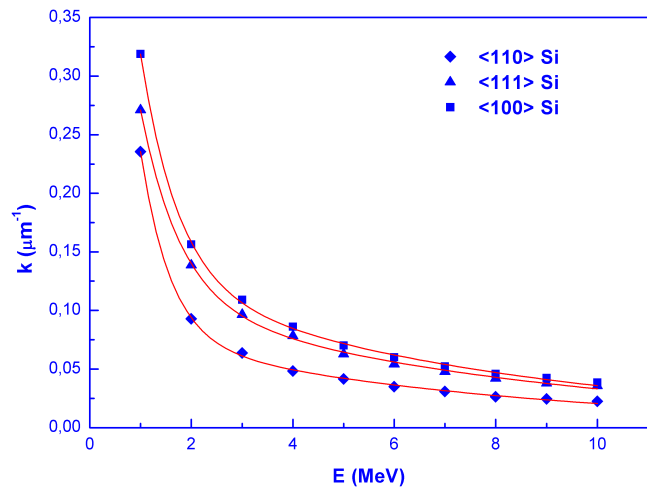
$$N_d = N_o \frac{e^{-\exp(-k(x-x_c))} - e^{-\exp(kx_c)}}{1 - e^{-\exp(kx_c)}}$$

**Exponential
dechanneling function**

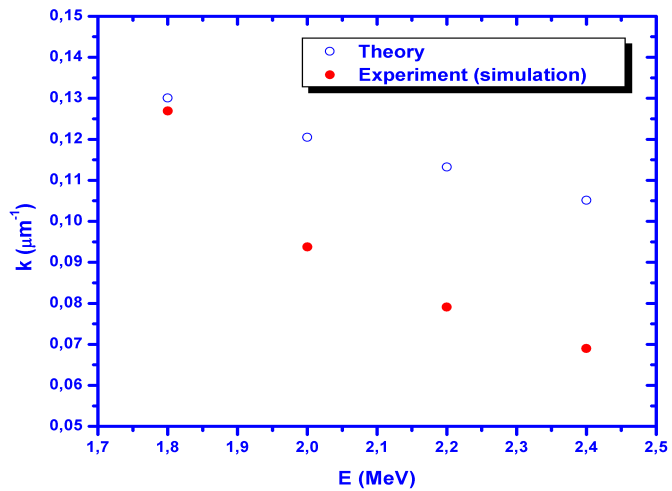
$$N_d = N_o (1 - e^{-kx})$$

Results

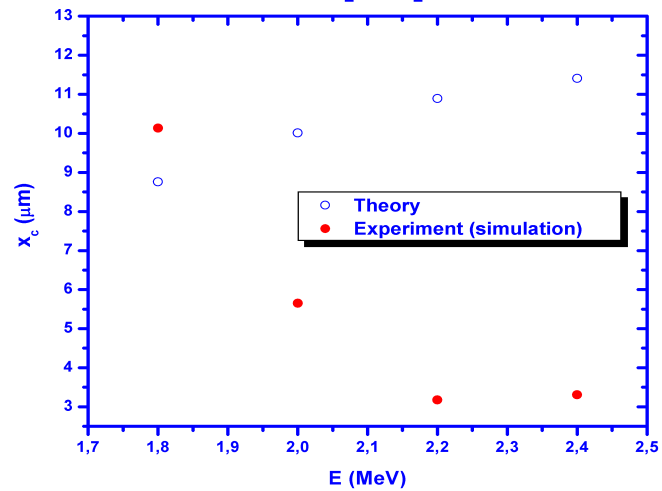




Si [110]

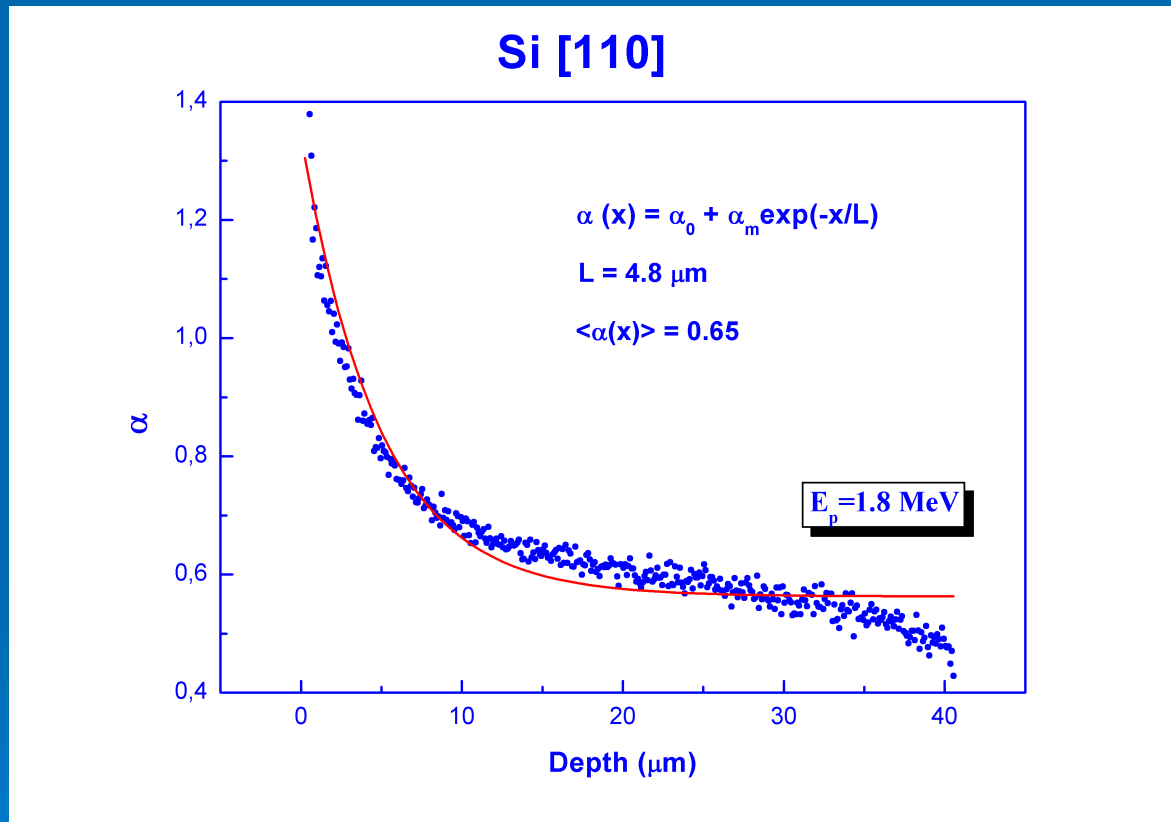


Si [110]



Energy loss of channeled ions

$$S_{\text{ch}} = \alpha(x) S_{\text{ran}}$$



Thank you for your attention

